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Strain effects on exciton resonance energies of ZnO epitaxial layers

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Magnitudes of strain in ZnO epitaxial layers grown on sapphire(0001) substrates under various growth conditions were experimentally determined by x-ray diffraction. We discuss the strain-induced energy shift on the exciton resonances, the results of which were analyzed theoretically using the Hamiltonian for the valence bands under in-plane biaxial strain. Comparative studies with GaN evidenced the advantages of ZnO in terms of sensitivity of the strain-induced energy shift and of piezoelectric effect in heterostructures. © 2001 American Institute of Physics. [DOI: 10.1063/1.1398328]

Much effort has recently been devoted to the studies on ZnO epitaxy due to the potential application as semiconductor laser diodes. This wide-gap semiconductor ensures an excitonic effect, which can be utilized at temperatures well above room temperature.\textsuperscript{1–3} Therefore, a lower pumping threshold for the gain emergence can be expected, in principle, if an exciton–related recombination rather than an electron-hole plasma recombination is used. An example of the latter is an In\textsubscript{0.53}Ga\textsubscript{0.47}N laser.\textsuperscript{4} ZnO epilayers oriented in the c-axis direction suffer from biaxial strain due to the mismatch of lattice constants between the epilayer and the substrate. Quantum well (QW) structures also suffer from a certain amount of strain. These strains may induce, for example, the formation of dark-line defects and a piezoelectric effect as discussed in the studies on ZnSe or GaN optoelectric devices. These defects tend to shorten the operational lifetime of the device, while the piezoelectric effect can lead to a reduction in the oscillator strength for excitonic transition. It should be noted that since the stimulated emission and/or laser action in ZnO related materials are of excitonic origin, the strain never becomes advantageous for reducing the gain threshold.

The in-plane lattice constant of sapphire(0001) substrate is largely mismatched with that of ZnO (18%). However, the actual amount of strain depends on the epitaxy mechanism and hence growth conditions, e.g., growth and annealing temperatures. It is important to achieve deeper understanding of the electronic structures of ZnO under in-plane biaxial strain, in particular, the strain dependencies of the exciton resonance energies.

In this letter, we present the optical properties of strained ZnO epilayers. The exciton resonance energies were estimated as a function of strain. These experimental results were analyzed using the strain Hamiltonian.

The samples were nominally undoped submicron-thick ZnO(0001) epilayers, which were grown on sapphire(0001) substrates by laser molecular-beam epitaxy. To control the lattice strain systematically, we used various types of samples at various growth and annealing temperatures. Reflection spectra were taken at 4.2 K using a xenon lamp as an excitation source. The spectral resolution was 1.5 meV.

Figures 1(a) and 1(b) show the annealing temperature dependence of the lattice constants of c and a axes in two typical ZnO epilayers and the relationship between c- and a-lattice constants, respectively. These were measured using the four-axis x-ray diffraction. The residual strain along the a- and c-axes were estimated by $\varepsilon_{xx} = (a - a_0) / a_0$ and $\varepsilon_{zz} = (c - c_0) / c_0$, where $a_0$ and $c_0$ are, respectively, the lattice constants in the unstrained crystal and taken as $a_0 = 3.2505$ and $c_0 = 5.2048$ Å. Since there is the relationship of $\varepsilon_{zz} = -2(C_{13}/C_{33}) \varepsilon_{xx}$ (in-plane biaxial strain), we define the Poisson ratio as $\nu = C_{13}/C_{33}$. Here, $C_{ij}$ ($i = 1–3$) denote the components of the elastic stiffness constants. One can deduce, $\nu = 0.5$ from the fitting shown in Fig. 1(b). Our estimated value is closer to that obtained in a bulk\textsuperscript{5} ($\nu = 0.50$) rather than that in a sputtered film\textsuperscript{5} ($\nu = 0.40$).

Figure 2 shows a reflection spectrum in a strained ZnO taken at 4.2 K. Three transitions labeled “A,” “B,” and “C,” which correspond to transitions from respective valence bands to the conduction band, can be seen. In Wurtzite-type II–IV compounds, three exciton series (A, B, and C) that are formed from the s-like ($\Gamma_{7u}^-$) conduction band and the three p-like ($\Gamma_{7v}^+$, $\Gamma_{9v}^+$, and $\Gamma_{7v}^-$) valence bands (cf. inset of Fig. 2), are observed.\textsuperscript{6,7} A and B transitions are allowed for light polarization perpendicular to the c axis, while the C transition is essentially allowed for polarization parallel to the c axis. Because of the c-axis orientation, A and B transitions are dominant.

The resonance energies ($E_A$ and $E_B$) were summarized in Fig. 3 as functions of strain, $\varepsilon_{zz}$ (strain parallel to the c axis).
The fitting results reported for GaN layers are also plotted.\(^8\) Energies of \(E_A\) and \(E_B\) are both linearly increasing functions of strain. The exciton energies of GaN show a complicated and nonlinear behavior on strain. Inhomogeneity of the strain inside the epilayers or QWs induces an inhomogeneous broadening of energy distribution of the exciton states in GaN. Such a strain insensitivity inherent to ZnO conserves the width of exciton energy states even if the strain distributes inhomogeneously inside the samples. We now consider the reason of this difference in the strain dependence.

For this purpose, we fit the experimental results with the equations derived by Rowe et al.\(^7\) The equations for the strain dependence have been obtained from the strain Hamiltonian.\(^10\),\(^11\) Keeping only terms up to the second order in the strain and within a cubic approximation, the energies for A and B exciton states are

\[
E_A^1 = E_A^0 + \delta_1 + \alpha_+ \delta_2 - \alpha_- \delta_2^2 / (E_C^0 - E_A^0),
\]

and

\[
E_B^1 = E_B^0 + \delta_1 + \alpha_- \delta_2,
\]

where \(\delta_1 = (D_1 - D_2 / \nu) e_{zz}\), \(\delta_2 = (D_2 - D_4 / \nu) e_{zz}\), and \(2 \alpha_n = 1 \pm [\Delta_1 - \Delta_2] [(\Delta_1 - \Delta_2)^2 + 8 \Delta_2^2]^{-1/2}\), with \(E_i^0 (i = A - C)\) and \(\nu\) are deformation potential constants and the earlier-mentioned Poisson ratio, respectively. Quantities \(\Delta_1\) and \(\Delta_2\) are crystal-field and spin-orbit splittings, respectively. The difference in the strain dependence between ZnO and GaN is attributed to the difference in the magnitude of the proportional coefficient of the fourth term of Eq. (1), especially \(\alpha_+ \alpha_-\). Note, symmetries of these valence bands ("valence band ordering")\(^12\) are reversed between ZnO and GaN due to the negative spin-orbit splitting.\(^13\) Table I shows the values\(^13\) of \(\Delta_1\), \(\Delta_2\), and \(\alpha_+ \alpha_-\) of GaN are 38 times of magnitude larger than that of ZnO. The difference in the sign between \(\Delta_1\) and \(\Delta_2\) in ZnO results in the smaller value of \(\alpha_+ \alpha_-\). We obtained the following parameters: \(D_1 - D_2 / \nu = 167\) and \(D_3 - D_4 / \nu = -166\).

\[\text{TABLE I. Crystal-field (}\Delta_1\text{), spin-orbit splitting related energies (}\Delta_2\text{), and } \alpha_+ \alpha_- \text{ in Eq. (1) of ZnO and GaN are shown.}\]

<table>
<thead>
<tr>
<th>Material</th>
<th>(\Delta_1) (meV)</th>
<th>(\Delta_2) (meV)</th>
<th>(\alpha_+ \alpha_-)</th>
</tr>
</thead>
<tbody>
<tr>
<td>ZnO(^a)</td>
<td>40.8</td>
<td>-1.57</td>
<td>(2.71 \times 10^{-3})</td>
</tr>
<tr>
<td>GaN(^b)</td>
<td>22</td>
<td>5</td>
<td>(1.0 \times 10^{-1})</td>
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\(^a\)From Ref. 14.

\(^b\)From Ref. 8.
In summary, the growth condition dependence of strain in ZnO epilayers on sapphire(0001) substrates was experimentally estimated by determining the lattice constants with an x-ray diffraction technique. Exciton resonance energies were experimentally determined as functions of strain by measuring the reflection spectra 4.2 K. The excitonic energies in ZnO are insensitive to the influence of strain compared with those in GaN. We described the advantage of ZnO:MgZnO and CdZnO:MgZnO QWs in terms of small strain (i.e., piezoelectric field), which is compared to the case of GaN-related QWs.


11 The exciton binding energies are dominated by the conduction band mass, and hence the energy differences in the three ground-state excitons are due to the splitting of the valence band by the hexagonal crystal-field and the spin-orbit interaction.


13 We follow the valence band ordering of Thomas and Hopfield (Refs. 6 and 7) in this work. There has been considerable controversy regarding this order. See the recent article by Reynolds et al. (Ref. 12). Rowe et al. have investigated the effects of static uniaxial compressive stress on the valence band characteristics of bulk ZnO and supported the Thomas-Hopfield interpretation (Ref. 9). From our study, the sign of the splitting (Ref. 6) could not be determined because we could not access the strain range in which the nonlinearity on the strain effect becomes negligible.


